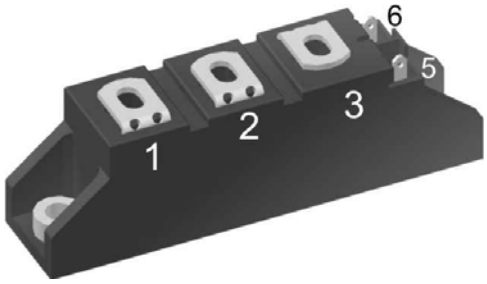
Thyristor Module

V_{RRM} = 2x 800V
I_{TAV} = 21A
V_T = 1.32V

Phase leg

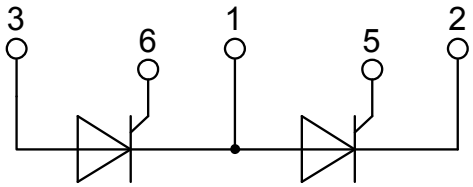
Part number

MCC21-08io8B



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

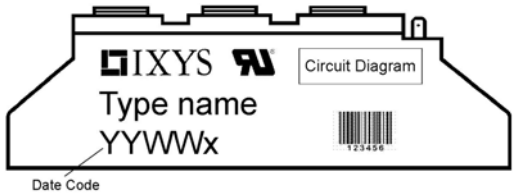
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			900	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			800	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 800 V	T_{VJ} = 25°C			100	µA
		$V_{R/D}$ = 800 V	T_{VJ} = 125°C			5	mA
V_T	*forward voltage drop*	I_T = 45 A	T_{VJ} = 25°C			1.31	V
		I_T = 90 A				1.64	V
		I_T = 45 A	T_{VJ} = 125°C			1.32	V
		I_T = 90 A				1.74	V
I_{TAV}	*average forward current*	T_C = 85°C	T_{VJ} = 125°C			21	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				33	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 125°C			0.85	V
r_T	*slope resistance* }					15	mΩ
R_{thJC}	*thermal resistance junction to case*					1.1	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.20		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			90	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			320	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			345	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			270	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			295	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			510	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			495	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			365	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			360	A²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		22		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 125°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 125°C; f = 50 Hz repetitive,	I_T = 45 A			150	A/µs
		t_P = 200 µs; di_G/dt = 0.45 A/µs;					
		I_G = 0.45A; V_D = ⅔ V_{DRM} non-repet.,	I_T = 21 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1	V
			T_{VJ} = -40°C			1.2	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			65	mA
			T_{VJ} = -40°C			80	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			0.2	V
I_{GD}	*gate non-trigger current*					5	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			150	mA
		I_G = 0.3A; di_G/dt = 0.3 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			100	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.3A; di_G/dt = 0.3 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 15 A; V_D = ⅔ V_{DRM}	T_{VJ} = 125°C		150		µs
		di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 300 µs					

Package TO-240AA					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					200	A
T_{stg}	*storage temperature*				-40		125	°C
T_{VJ}	*virtual junction temperature*				-40		125	°C
Weight						90		g
M_D	*mounting torque*				2.5		4	Nm
M_T	*terminal torque*				2.5		4	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	13.0	9.7			mm
$d_{Spb/Apb}$			*terminal to backside*	16.0	16.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3600			V
		t = 1 minute			3000			V

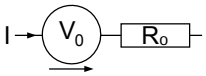


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC21-08io8B	MCC21-08io8B	Box	6	

Similar Part	Package	Voltage class
MCMA25P1200TA	TO-240AA-1B	1200
MCMA35P1200TA	TO-240AA-1B	1200

Equivalent Circuits for Simulation

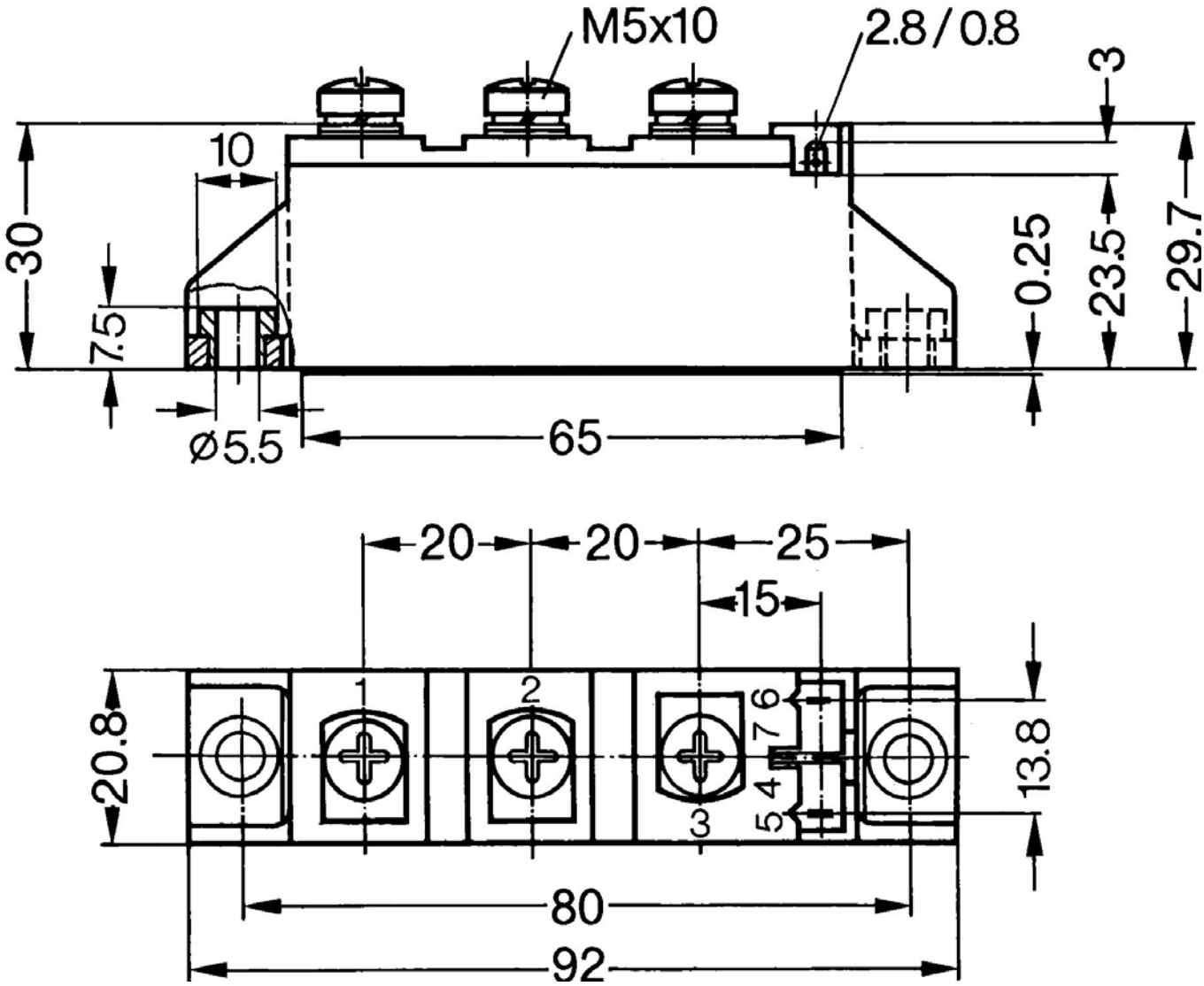
** on die level* T_{VJ} = 125 °C

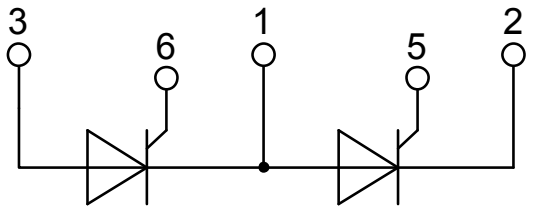


Thyristor

$V_{0\,max}$	*threshold voltage*	0.85	V
$R_{0\,max}$	*slope resistance **	13.8	mΩ

Outlines TO-240AA





Thyristor

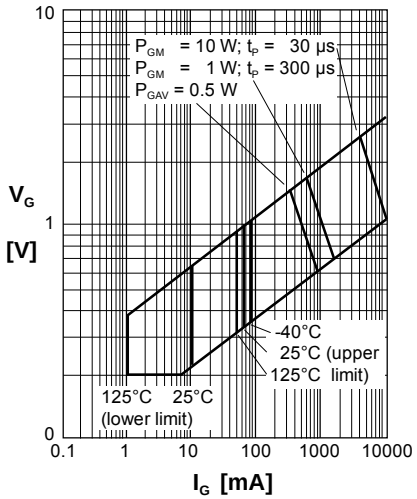


Fig. 1 Gate trigger characteristics

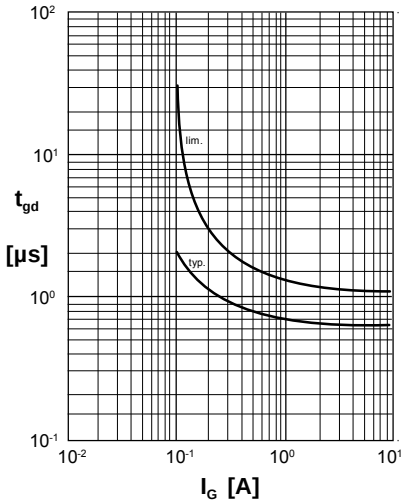


Fig. 2 Gate trigger delay time

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